

# P-Channel Enhancement-Mode Vertical DMOS FET

#### Features

- High input impedance and high gain
- Low power drive requirement
- Ease of paralleling
- Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- Free from secondary breakdown

#### Applications

- Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic systems
- Analog switches
- Power management
- Telecom switches

# **Ordering Information**

Part Number	Package Option	Packing
TP0610T-G	TO-236AB (SOT-23)	3000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package. Contact factory for Wafer / Die availablity.

Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

# Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	BV <sub>DGS</sub>
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

# Typical Thermal Resistance

Package	<b>θ</b> <sub>ja</sub>
TO-236AB (SOT-23)	203°C/W

## **General Description**

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### **Product Summary**

$BV_{DSS}/BV_{DGS}$	R <sub>DS(ON)</sub> (max)	l <sub>D(ON)</sub> (min)			
-60V	10Ω	-50mA			

# **Pin Configuration**



#### **Product Marking**

T50W

W = Code for week sealed \_\_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or () TO-236AB (SOT-23)

# TP0610T

### **Thermal Characteristics**

Package	Ι <sub>D</sub> (continuous) <sup>†</sup>	Ι <sub>D</sub> (pulsed)	Power Dissipation @T <sub>A</sub> = 25°C	l <sub>DR</sub> <sup>†</sup>	I <sub>DRM</sub>
TO-236AB (SOT-23)	-120mA	-400mA	0.36W	-120mA	-400mA

Notes:

 $\uparrow I_{D}$  (continuous) is limited by max rated  $T_{i}$ .

### **Electrical Characteristics** (*T<sub>A</sub>* = 25°C unless otherwise specified)

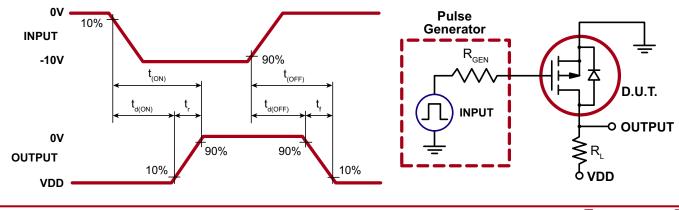
Sym	Parameter		Тур	Max	Units	Conditions		
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	-60	-	-	V	V <sub>GS</sub> = 0V, Ι <sub>D</sub> = -10μΑ		
V <sub>GS(th)</sub>	Gate threshold voltage	-1.0	-	-2.4	V	$V_{GS} = V_{DS}, I_{D} = -1.0 \text{mA}$		
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	6.5	mV/ºC	$V_{GS} = V_{DS}, I_{D} = -1.0 \text{mA}$		
I <sub>GSS</sub>	Gate body leakage	-	-	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
			-	-1.0		$V_{GS}$ = 0V, $V_{DS}$ = Max Rating		
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	-200	μA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_A = 125^{\circ}C$		
I <sub>D(ON)</sub>	On-state drain current	-50	-	-	mA	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V		
D	Static drain-to-source on-state resistance		-	25	Ω	$V_{GS}$ = -4.5V, $I_{D}$ = -25mA		
R <sub>DS(ON)</sub>	Static drain-to-source on-state resistance		-	10	52	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA		
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	-	1.0	%/°C	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA		
G <sub>FS</sub>	Forward transconductance	60	-	-	mmho	V <sub>DS</sub> = -10V, I <sub>D</sub> = -100mA		
C <sub>ISS</sub>	Input capacitance	-	-	60		V <sub>GS</sub> = 0V,		
C <sub>oss</sub>	Common source output capacitance	-	-	30	pF	$V_{\rm DS}^{\rm o}$ = -25V,		
C <sub>RSS</sub>	Reverse transfer capacitance	-	-	10		f = 1.0 MHz		
t <sub>d(ON)</sub>	Turn-on delay time	-	-	10				
t <sub>r</sub>	Rise time	-	-	15		$V_{DD} = -25V,$		
t <sub>d(OFF)</sub>	Turn-off delay time	-	-	15	ns	$I_{D} = -180 \text{mA},$ $R_{GEN} = 25\Omega$		
t <sub>r</sub>	Fall time	-	-	20		GEN		
V <sub>SD</sub>	Diode forward voltage drop	-	-	-2.0	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = -120mA		
t <sub>rr</sub>	Reverse recovery time	-	400	-	ns	V <sub>GS</sub> = 0V, I <sub>SD</sub> = -400mA		

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

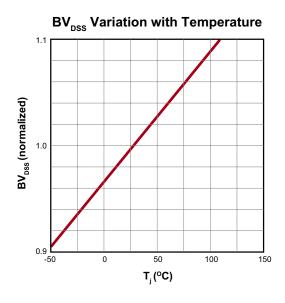
2. All A.C. parameters sample tested.

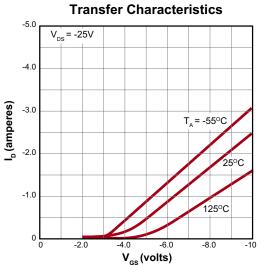
### Switching Waveforms and Test Circuit



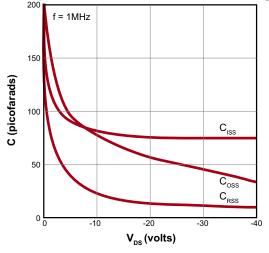
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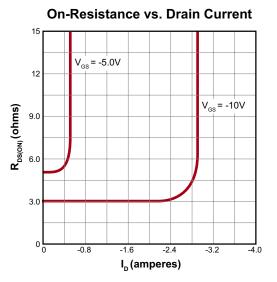
#### **Typical Performance Curves**



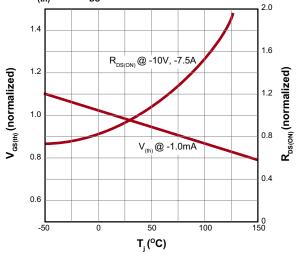


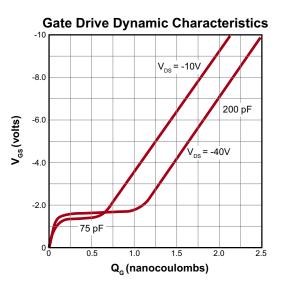








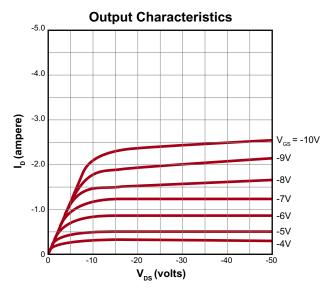




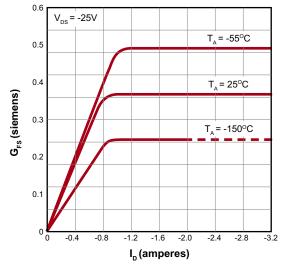
#### Doc.# DSFP-TP0610T C081313

# **TP0610T**

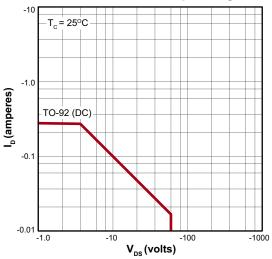
#### Typical Performance Curves (cont.)

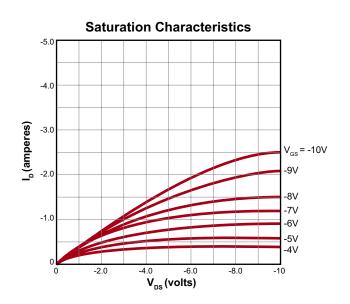


Transconductance vs. Drain Current

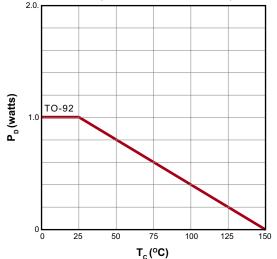


**Maximum Rated Safe Operating Area** 

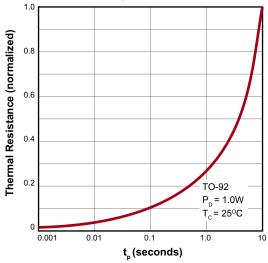




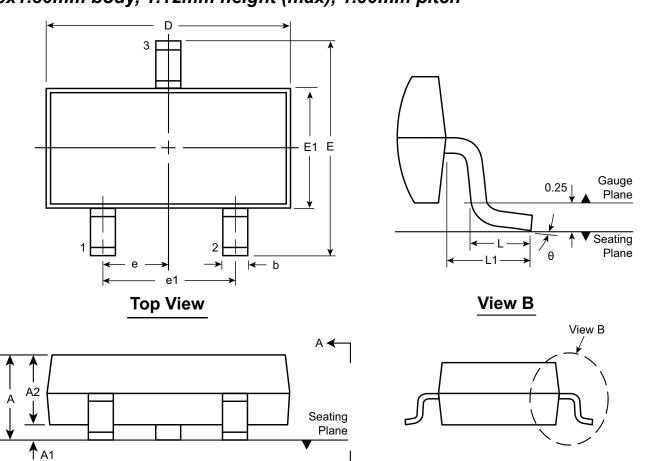
Power Dissipation vs. Case Temperature



Thermal Response Characteristics



# 3-Lead TO-236AB (SOT-23) Package Outline (T) 2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



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Symb	ol	Α	A1	A2	b	D	E	E1	е	e1	L	L1	θ		
Dimension	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	4.00	0.20†	0.54	<b>0</b> 0		
Dimension (mm)	NOM	-	-	0.95	-	2.90	-	1.30	0.95 BSC	1.90 BSC	0.50	0.54 REF	-		
(((((((((((((((((((((((((((((((((((((((	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	воо	BSC	000	530	0.60		<b>8</b> 0

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JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

Side View

*†* This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>http://www.supertex.com/packaging.html</u>.)

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